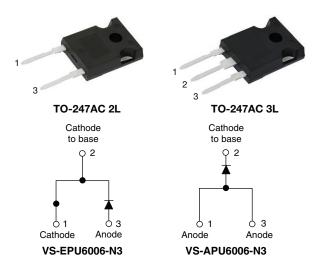
VS-EPU6006-N3, VS-APU6006-N3

Vishay Semiconductors

Ultrafast Soft Recovery Diode, 60 A FRED Pt®



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PRIMARY CHARACTERISTICS							
I _{F(AV)}	60 A						
V _R	600 V						
V _F at I _F	1.05 V						
t _{rr} typ.	32 ns						
T _J max.	175 °C						
Package	TO-247AC 2L, TO-247AC 3L						
Circuit configuration	Single						

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Designed and qualified according to JEDEC[®]-JESD 47



HALOGEN

FREE

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

VS-EPU60/VS-APU60... series are the state of the art ultrafast recovery rectifiers designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, welding, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Repetitive peak reverse voltage	V _{RRM}		600	V
Average rectified forward current in DC	I _{F(AV)}	T _C = 116 °C	60	٨
Single pulse forward current	I _{FSM}	$T_{C} = 25 \ ^{\circ}C, t_{p} = 10 \ ms$	600	A
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	
		I _F = 60 A	-	1.2	1.5	V
Forward voltage	V _F	I _F = 60 A, T _J = 125 °C	-	1.1	1.3	
		I _F = 60 A, T _J = 175 °C	-	1.05	1.2	
Reverse leakage current	1	V _R = V _R rated	-	-	30	
neverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	200	μA
Junction capacitance	CT	V _R = 600 V	-	38	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	32	43	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	110	-	ns
		T _J = 125 °C		-	200	-	
Peak recovery current	I _{RRM}	T _J = 25 °C	$I_F = 60 A$	-	10	-	А
Feak recovery current		$T_{J} = 125 \text{ °C}$ $V_{R} = 200 \text{ V}$	-	19	-	~	
Deverse measure channel 0	0	T _J = 25 °C		-	530	-	
Reverse recovery charge	rge Q _{rr} -	T _J = 125 °C		-	1900	-	nC

THERMAL - MECHAN	THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	0.65			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	°C/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-			
Weight			-	6	-	g		
Weight			-	0.21	-	oz.		
Mounting torque			6 (5)	-	1.2 (10)	kgf. cm (lbf ⋅ in)		
Marking daviaa		Case style TO-247AC 2L		EPU	6006			
Marking device		Case style TO-247AC 3L		APU6006				



VS-EPU6006-N3, VS-APU6006-N3

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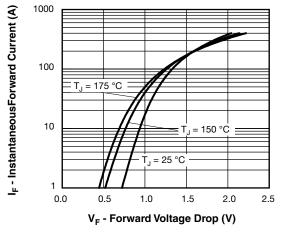


Fig. 1 - Typical Forward Voltage Drop Characteristics

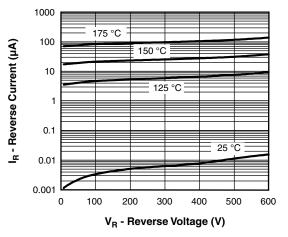


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

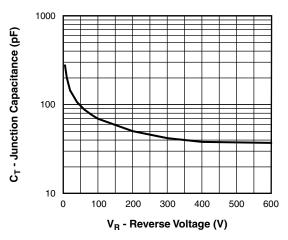
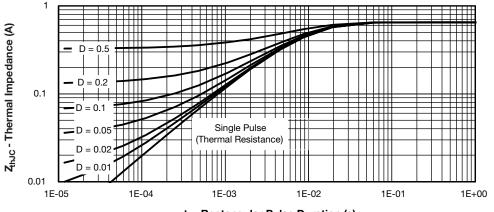


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



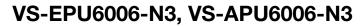
t₁ - Rectangular Pulse Duration (s)

Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

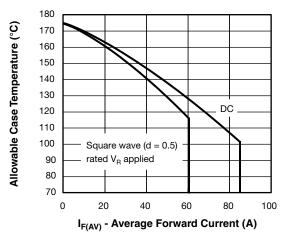
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Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

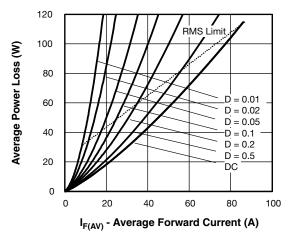


Fig. 6 - Forward Power Loss Characteristics

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

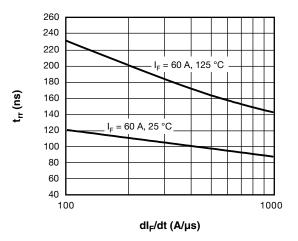


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

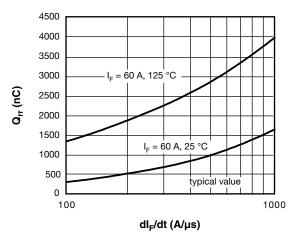


Fig. 8 - Typical Stored Charge vs. dl_F/dt

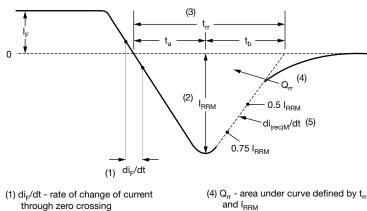
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VS-EPU6006-N3, VS-APU6006-N3





(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 $I_{\rm RRM}$ and 0.50 $I_{\rm RRM}$ extrapolated to zero current.

and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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Device code	VS-	E	Ρ	U	60	06	-N3	
	1	2	3	4	5	6	7	
	1	- Circ A = E =	cuit conf single o	nicondu figuration diode, 3 diode, 2 7AC	n: pins	oduct		
	4			st recove	-			
	5 6			de (60 = de (06 =				
	7		•	ntal digit	,			
		-N3	3 = halog	gen-free	, RoHS	-compli	ant, and	totally lead

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-EPU6006-N3	25	500	Antistatic plastic tube			
VS-APU6006-N3	25	500	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS						
Dimensions	TO-247AC 2L	www.vishay.com/doc?96144				
Dimensions	TO-247AC 3L	www.vishay.com/doc?96138				
Port marking information	TO-247AC 2L	www.vishay.com/doc?95648				
Part marking information	TO-247AC 3L	www.vishay.com/doc?95007				

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